# Alberta Bonanni

## List of Publications by Year in descending order

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|---|---|---|---|
| 150 papers | 2,417 citations | 230014 27 h-index | 274796 44 g-index |
| 152 all docs | 152 docs citations | 152 times ranked | 2697 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Dilute Magnetic Materials. , 2021, , 1-56. | | 1 |
| 2 | Cross-plane thermal conductivity of GaN/AlN superlattices. Applied Physics Letters, 2021, 118, . | 1.5 | 8 |
| 3 | Unravelling the local crystallographic structure of ferromagnetic $$gamma '$$-$$hbox {Ga}_y hbox {Fe}_{4-y}$$N nanocrystals embedded in GaN. Scientific Reports, 2021, 11, 2862. | 1.6 | 5 |
| 4 | Direct-ARPES and STM Investigation of FeSe Thin Film Growth by Nd:YAG Laser. Coatings, 2021, 11, 276. | 1.2 | 5 |
| 5 | Low temperature and high magnetic field performance of a commercial piezo-actuator probed via laser interferometry. Review of Scientific Instruments, 2021, 92, 035002. | 0.6 | 2 |
| 6 | Positive Magnetoresistance and Chiral Anomaly in Exfoliated Type-II Weyl Semimetal Td-WTe2. Nanomaterials, 2021, 11, 2755. | 1.9 | 2 |
| 7 | Dilute Magnetic Materials. , 2021, , 923-978. | | 0 |
| 8 | Femtosecond phononic coupling to both spins and charges in a room-temperature antiferromagnetic semiconductor. Physical Review B, 2021, 104, . | 1.1 | 10 |
| 9 | Out-of-Plane Magnetic Anisotropy in Ordered Ensembles of FeyN Nanocrystals Embedded in GaN. Materials, 2020, 13, 3294. | 1.3 | 10 |
| 10 | Photoluminescence and Stoichiometry Correlation in Nanocrystalline EuOx Thin Films: Tunable Color Emission. Journal of Physical Chemistry C, 2020, 124, 15434-15439. | 1.5 | 12 |
| 11 | Families of magnetic semiconductors â€" an overview. Journal of Semiconductors, 2019, 40, 080301. | 2.0 | 52 |
| 12 | Ferromagnetic phase transition in topological crystalline insulator thin films: Interplay of anomalous Hall angle and magnetic anisotropy. Physical Review B, 2019, 100, . | 1.1 | 11 |
| 13 | Resonance Raman Spectroscopy of Mn-Mgk Cation Complexes in GaN. Crystals, 2019, 9, 235. | 1.0 | 5 |
| 14 | Tuning the Size, Shape and Density of Î³â€²-GayFe4â^'yN Nanocrystals Embedded in GaN. Crystals, 2019, 9, 50. | 1.0 | 6 |
| 15 | Magnetotransport in phase-separated (Ga,Fe)N with Î³â€²â^'GayFe4â^'yN nanocrystals. Physical Review B, 2019, 99, . | 1.1 | 10 |
| 16 | 57Fe MÃ¶ssbauer study of epitaxial TiN thin film grown on MgO (1â€¯0â€¯0) by magnetron sputtering. Applied Surface Science, 2019, 464, 682-691. | 3.1 | 5 |
| 17 | Influence of Mn co-doping on the magnetic properties of planar arrays of Ga<sub>x</sub>Fe<sub>4â^'x</sub>N nanocrystals in a GaN matrix. Physical Chemistry Chemical Physics, 2018, 20, 25411-25420. | 1.3 | 6 |
| 18 | Resonant excitation of infrared emission in GaN:(Mn,Mg). Physical Review B, 2018, 97, . | 1.1 | 4 |

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| 19 | Europium monoxide nanocrystalline thin films with high near-infrared transparency. Applied Surface Science, 2018, 456, 980-984. | 3.1 | 12 |
| 20 | Effects of dielectric stoichiometry on the photoluminescence properties of encapsulated WSe2 monolayers. Nano Research, 2018, 11, 1399-1414. | 5.8 | 12 |
| 21 | Industrial-scale sputter deposition of molybdenum oxide thin films: Microstructure evolution and properties. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, . | 0.9 | 18 |
| 22 | All-nitride AlxGa1â^'xN:Mn/GaN distributed Bragg reflectors for the near-infrared. Scientific Reports, 2017, 7, 42697. | 1.6 | 9 |
| 23 | Processing and charge state engineering of MoOx. AIP Advances, 2017, 7, . | 0.6 | 17 |
| 24 | Non-reactive dc magnetron sputter deposition of Mo-O thin films from ceramic MoOx targets. Surface and Coatings Technology, 2017, 332, 80-85. | 2.2 | 12 |
| 25 | Raman and IR-ATR spectroscopy studies of heteroepitaxial structures with a GaN:C top layer. Journal Physics D: Applied Physics, 2017, 50, 365103. | 1.3 | 9 |
| 26 | Decoupling of epitaxyâ€related trapping effects in AlGaN/GaN metalâ€“insulator semiconductor highâ€electronâ€mobility transistors. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1222-1228. | 0.8 | 1 |
| 27 | Controlling a three dimensional electron slab of graded AlxGa1â^'xN. Applied Physics Letters, 2016, 108, . | 1.5 | 9 |
| 28 | Characterization of AlN/AlGaN/GaN:C heterostructures grown on Si(111) using atom probe tomography, secondary ion mass spectrometry, and vertical current-voltage measurements. Journal of Applied Physics, 2016, 119, . | 1.1 | 13 |
| 29 | Rashba semiconductor as spin Hall material: Experimental demonstration of spin pumping in wurtzite<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-GaN:Si. Physical Review B, 2016, 94, . | 1.1 | 10 |
| 30 | Stretching magnetism with an electric field in a nitride semiconductor. Nature Communications, 2016, 7, 13232. | 5.8 | 33 |
| 31 | Two-Probe Measurements of Electron Transport in GaN:Si/(Ga,Mn)N/GaN:Si Spin Filter Structures. Acta Physica Polonica A, 2016, 130, 1196-1198. | 0.2 | 2 |
| 32 | Upper bound for the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>s</mml:mi><mml:mtext>â^'</mml:mtext><mml:mi>d</m integral in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-(Ga,Mn)N:Si from polarization dependent<mml:math Physical Review B, 2015, 91, . | 1.1 | 8 |
| 33 | <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Al</mml:mi><mml:mi>x</mml:mi></mml:ms mathvariant="normal">N</mml:mi></mml:mrow></mml:math>probed by x-ray absorption and emission spectroscopy, high-resolution microscopy, x-ray diffraction, and first-principles calculations. Physical Review B, 2015, 92, . | 1.1 | 2 |
| 34 | Spinodal nanodecomposition in semiconductors doped with transition metals. Reviews of Modern Physics, 2015, 87, 1311-1377. | 16.4 | 152 |
| 35 | Analytical electron microscopy study on gallium nitride systems doped with manganese and iron. Semiconductor Science and Technology, 2015, 30, 035002. | 1.0 | 0 |
| 36 | Mn as Surfactant for the Self-Assembling of Al<sub>x</sub>Ga<sub>1â€“x</sub>N/GaN Layered Heterostructures. Crystal Growth and Design, 2015, 15, 587-592. | 1.4 | 14 |

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| 37 | Impact of residual carbon impurities and gallium vacancies on trapping effects in AlGaN/GaN metal insulator semiconductor high electron mobility transistors. Applied Physics Letters, 2015, 107, . | 1.5 | 32 |
| 38 | Experimental determination of Rashba spin-orbit coupling in wurtzite<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-GaN:Si. Physical Review B, 2014, 89, . | 1.1 | 27 |
| 39 | Planar array of self-assembled GaxFe4â^'xN nanocrystals in GaN: magnetic anisotropy determinedviaferromagnetic resonance. Nanotechnology, 2014, 25, 395704. | 1.3 | 8 |
| 40 | Characterization of Fe-N nanocrystals and nitrogenâ€“containing inclusions in (Ga,Fe)N thin films using transmission electron microscopy. Journal of Applied Physics, 2013, 114, . | 1.1 | 8 |
| 41 | Relation between exciton splittings, magnetic circular dichroism, and magnetization in wurtzite Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>N. Physical Review B, 2013, 88, . | 1.1 | 8 |
| 42 | Phase diagram and critical behavior of the random ferromagnet Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Mn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>N. Physical Review B, 2013, 88, . | 1.1 | 53 |
| 43 | Functional Mnâ€“Mgk cation complexes in GaN featured by Raman spectroscopy. Applied Physics Letters, 2013, 103, . | 1.5 | 9 |
| 44 | Substrate-Driven Formation of Bidimensional Arrays of Co Nanocrystals in TiO<sub>2</sub> Thin Films. Journal of Physical Chemistry C, 2013, 117, 687-691. | 1.5 | 2 |
| 45 | Manipulating Mnâ€“Mgk cation complexes to control the charge- and spin-state of Mn in GaN. Scientific Reports, 2012, 2, 722. | 1.6 | 43 |
| 46 | Planar arrays of magnetic nanocrystals embedded in GaN. Applied Physics Letters, 2012, 101, 081911. | 1.5 | 17 |
| 47 | Ga1â^'xMnxN epitaxial films with high magnetization. Applied Physics Letters, 2012, 101, . | 1.5 | 48 |
| 48 | Element-specific characterization of heterogeneous magnetism in (Ga,Fe)N films. Physical Review B, 2012, 85, . | 1.1 | 13 |
| 49 | Origin of low-temperature magnetic ordering in Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Mn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>N. Physical Review B, 2012, 85, . | 1.1 | 48 |
| 50 | Fe-Mg interplay and the effect of deposition mode in (Ga,Fe)N doped with Mg. Physical Review B, 2011, 84, . | 1.1 | 21 |
| 51 | (Nano)characterization of semiconductor materials and structures. Semiconductor Science and Technology, 2011, 26, 060301. | 1.0 | 5 |
| 52 | Effects ofs,p-dands-pexchange interactions probed by exciton magnetospectroscopy in (Ga,Mn)N. Physical Review B, 2011, 83, . | 1.1 | 21 |
| 53 | Experimental probing of exchange interactions between localized spins in the dilute magnetic insulator (Ga,Mn)N. Physical Review B, 2011, 84, . | 1.1 | 61 |
| 54 | Ohmic Contacts to p-GaN Using Au/Ni-Zn-O Metallization. Journal of Electrical Engineering, 2011, 62, . | 0.4 | 0 |

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| 55 | Columnar microstructure of nanocrystalline Ga1âˆ’xMnxN films deposited by reactive sputtering. Journal of Crystal Growth, 2011, 327, 209-214. | 0.7 | 9 |
| 56 | Compensation-dependence of magnetic and electrical properties in Ga1âˆ’xMnxP. Applied Physics Letters, 2011, 98, 012103. | 1.5 | 9 |
| 57 | Magnetooptical Properties of (Ga,Fe)N Layers. Acta Physica Polonica A, 2011, 120, 921-923. | 0.2 | 1 |
| 58 | Ohmic contacts to p-GaN Using Au/Ni-Mg-O Metallization. Journal of Electrical Engineering, 2010, 61, 378-381. | 0.4 | 4 |
| 59 | Embedded magnetic phases in (Ga,Fe)N: Key role of growth temperature. Physical Review B, 2010, 81, . | 1.1 | 41 |
| 60 | Structural and paramagnetic properties of dilute<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Ga</mml:mtext></mml:mrow><mml:mrow><mml:mn>1</mml:mn></mml:mr Physical Review B, 2010, 81, . | 1.1 | 70 |
| 61 | A story of high-temperature ferromagnetism in semiconductors. Chemical Society Reviews, 2010, 39, 528-539. | 18.7 | 122 |
| 62 | Local structure of (Ga,Fe)N and (Ga,Fe)N:Si investigated by x-ray absorption fine structure spectroscopy. Physical Review B, 2009, 79, . | 1.1 | 42 |
| 63 | Investigation of NiO x -based contacts on p-GaN. Journal of Materials Science: Materials in Electronics, 2008, 19, 855-862. | 1.1 | 14 |
| 64 | Bipolar Charge Transport in PCPDTBTâ€PCBM Bulkâ€Heterojunctions for Photovoltaic Applications. Advanced Functional Materials, 2008, 18, 1757-1766. | 7.8 | 156 |
| 65 | GaN:-Mg grown by MOVPE: Structural properties and their effect on the electronic and optical behavior. Journal of Crystal Growth, 2008, 310, 13-21. | 0.7 | 22 |
| 66 | In situ monitoring of periodic structures during MOVPE of III-nitrides. Journal of Crystal Growth, 2008, 310, 1607-1613. | 0.7 | 2 |
| 67 | Fe onto GaN(0001) grown in a full MOVPE process. Journal of Crystal Growth, 2008, 310, 1772-1776. | 0.7 | 3 |
| 68 | Phase-dependent distribution of Fe-rich nanocrystals in MOVPE-grown (Ga,Fe)N. Journal of Crystal Growth, 2008, 310, 3294-3298. | 0.7 | 13 |
| 69 | Periodic Mg distribution in GaN:Î´-Mg and the effect of annealing on structural and optical properties. Applied Surface Science, 2008, 255, 731-733. | 3.1 | 5 |
| 70 | Controlled Aggregation of Magnetic Ions in a Semiconductor: An Experimental Demonstration. Physical Review Letters, 2008, 101, 135502. | 2.9 | 106 |
| 71 | Observation of Strong-Coupling Effects in a Diluted Magnetic Semiconductor<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>âˆ’</mml:mo><mml:mi>x</mml:mi></mml:mr mathvariant="normal">N</mml:mi></mml:math>. Physical Review Letters, 2008, 100, 037204. | 2.9 | 51 |
| 72 | Effects of magnetic ions on optical properties: the case of (Ga, Fe)N. Journal of Physics Condensed Matter, 2008, 20, 454222. | 0.7 | 0 |

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| 73 | Microstructure of (Ga,Fe)N Films Grown by Metal-Organic Chemical Vapour Deposition. Springer Proceedings in Physics, 2008, , 77-80. | 0.1 | 0 |
| 74 | On the effect of periodic Mg distribution in GaN:Î´-Mg. Applied Physics Letters, 2007, 90, 142108. | 1.5 | 18 |
| 75 | Fourier analysis applied on in situ laser reflectometry during III-nitride metal organic chemical vapor deposition growth. Journal of Applied Physics, 2007, 101, 093501. | 1.1 | 3 |
| 76 | Ferromagnetic nitride-based semiconductors doped with transition metals and rare earths. Semiconductor Science and Technology, 2007, 22, R41-R56. | 1.0 | 88 |
| 77 | ParamagneticGaN:Feand ferromagnetic(Ga,Fe)N: The relationship between structural, electronic, and magnetic properties. Physical Review B, 2007, 75, . | 1.1 | 109 |
| 78 | In situ X-ray diffraction during MOCVD of III-nitrides: An optimized wobbling compensating evaluation algorithm. Journal of Crystal Growth, 2007, 298, 243-245. | 0.7 | 6 |
| 79 | In situ growth observation of GaN/AlGaN superlattice structures by simultaneous X-ray diffraction and ellipsometry. Journal of Crystal Growth, 2007, 308, 258-262. | 0.7 | 5 |
| 80 | Photoluminescence and Hall studies of GaN:Fe and (Ga,Fe)N:Mg layers. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 86-91. | 0.8 | 2 |
| 81 | In situ Xâ€ray diffraction during MOCVD of IIIâ€nitrides. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2798-2803. | 0.8 | 3 |
| 82 | Auger electron spectroscopy of Au/NiOx contacts on p-GaN annealed in N2 and O2+N2 ambients. Applied Surface Science, 2007, 253, 3174-3180. | 3.1 | 7 |
| 83 | In-situ and real-time monitoring of MOCVD growth of III-nitrides by simultaneous multi-wavelength-ellipsometry and X-ray-diffraction. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1704-1707. | 0.8 | 10 |
| 84 | Doping of GaN with Fe and Mg for spintronics applications. Physica Status Solidi (B): Basic Research, 2006, 243, 1701-1705. | 0.7 | 19 |
| 85 | Magnetic properties of a new spintronic materialâ€"GaN:Fe. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 126, 222-225. | 1.7 | 28 |
| 86 | Simultaneous determination of composition and growth rate of MOCVD nitrides by in situ multiple wavelength ellipsometry. Journal of Crystal Growth, 2005, 275, e1763-e1766. | 0.7 | 5 |
| 87 | Atomic force microscopy analysis of morphology of the upper boundaries of GaN thin films prepared by MOCVD. Vacuum, 2005, 80, 53-57. | 1.6 | 3 |
| 88 | In-situ multiple wavelength ellipsometry for real time process characterization of nitride MOCVD. AIP Conference Proceedings, 2005, , . | 0.3 | 0 |
| 89 | Optical characterization of double layers containing epitaxial ZnSe and ZnTe films. Journal of Modern Optics, 2005, 52, 583-602. | 0.6 | 9 |
| 90 | Characterization of metalorganic chemical vapor deposition growth of cubic GaN by in situ x-ray diffraction. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2165. | 1.6 | 5 |

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| 91 | In-situ growth monitoring by spectroscopy ellipsometry of MOCVD cubic-GaN(001). Thin Solid Films, 2004, 455-456, 684-687. | 0.8 | 4 |
| 92 | On-line growth control of MOCVD deposited GaN and related ternary compounds via spectroscopic ellipsometry and X-ray diffraction. Physica Status Solidi A, 2004, 201, 2259-2264. | 1.7 | 0 |
| 93 | Optical properties of ZnTe films prepared by molecular beam epitaxy. Thin Solid Films, 2004, 468, 193-202. | 0.8 | 30 |
| 94 | In situ optical analysis of low temperature MOCVD GaN nucleation layer formation via multiple wavelength ellipsometry. Journal of Crystal Growth, 2004, 272, 106-110. | 0.7 | 1 |
| 95 | In situ spectroscopic ellipsometry of MOCVD-grown GaN compounds for on-line composition determination and growth control. Journal of Crystal Growth, 2003, 248, 211-215. | 0.7 | 24 |
| 96 | Atomic Force Microscopy Characterization of ZnTe Epitaxial Thin Films. Japanese Journal of Applied Physics, 2003, 42, 4706-4709. | 0.8 | 13 |
| 97 | Magnetization and spin distribution of single sub-monolayers of MnTe in semiconductor quantum wells. Physical Review B, 2003, 68, . | 1.1 | 5 |
| 98 | Optical characterization of ZnSe thin films. , 2003, , . | | 0 |
| 99 | Virtual interface approximation model applied to spectroscopic ellipsometry for on-line composition determination of metalorganic chemical vapor deposition grown ternary nitrides. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1825. | 1.6 | 9 |
| 100 | Influence of overlayers on determination of the optical constants of ZnSe thin films. Journal of Applied Physics, 2002, 92, 1873-1880. | 1.1 | 39 |
| 101 | Collective Dimer Stress Induced Dichroism in II-VI Semiconductors. Physica Status Solidi (B): Basic Research, 2002, 229, 155-159. | 0.7 | 0 |
| 102 | In Situ Optical Techniques for Monitoring the Formation of Nanostructures. Physica Status Solidi (B): Basic Research, 2002, 232, 13-23. | 0.7 | 2 |
| 103 | Reflectance difference spectroscopy during CdTe/ZnTe interface formation. Applied Surface Science, 2002, 190, 307-310. | 3.1 | 2 |
| 104 | In situspectroscopic ellipsometry as a sensor for hard coatings and steel nitriding. Surface and Interface Analysis, 2002, 34, 681-685. | 0.8 | 3 |
| 105 | On the origin of resonance features in reflectance difference data of silicon. Applied Surface Science, 2001, 175-176, 769-776. | 3.1 | 27 |
| 106 | Influence of anisotropic in-plane strain on critical point resonances in reflectance difference data. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1650. | 1.6 | 10 |
| 107 | In situobservation of stress relaxation in CdTe/ZnTe heterostructures by reflectance-difference spectroscopy. Applied Physics Letters, 2001, 78, 3615-3617. | 1.5 | 17 |
| 108 | Zeeman mapping of probability densities in square quantum wells using ultranarrow probes. Springer Proceedings in Physics, 2001, , 467-468. | 0.1 | 0 |

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| 109 | Magnetization of single MnTe (sub)monolayers embedded in nonmagnetic quantum wells.. Springer Proceedings in Physics, 2001, , 216-217. | 0.1 | 0 |
| 110 | In situ reflectance difference spectroscopy of intra-Mn transitions in highly N-doped IIâ€“VI diluted magnetic semiconductors. Journal of Crystal Growth, 2000, 214-215, 163-166. | 0.7 | 7 |
| 111 | Carrier-induced ferromagnetic interactions in p-doped Zn(1â^'x)MnxTe epilayers. Journal of Crystal Growth, 2000, 214-215, 387-390. | 0.7 | 56 |
| 112 | Reflectance difference spectroscopy: a powerful tool for in situ investigations of IIâ€“VI compounds with Mn. Thin Solid Films, 2000, 367, 216-219. | 0.8 | 0 |
| 113 | In situ reflectance difference spectroscopy of p-type ZnTe:N grown by MBE. Thin Solid Films, 2000, 373, 41-45. | 0.8 | 1 |
| 114 | Indication of ferromagnetic ordering in p-Zn1â^'xMnxTe. Physica B: Condensed Matter, 2000, 284-288, 1177-1178. | 1.3 | 17 |
| 115 | Antiferromagnetic phase transition in a single MnTe monolayer. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 1006-1010. | 1.3 | 2 |
| 116 | In situ reflectance-difference spectroscopy of doped CdTe and ZnTe grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2224. | 1.6 | 7 |
| 117 | Zeeman mapping of probability densities in square quantum wells using magnetic probes. Physical Review B, 2000, 61, 15617-15620. | 1.1 | 8 |
| 118 | Surface-stress-induced optical bulk anisotropy. Physical Review B, 2000, 62, 13048-13052. | 1.1 | 30 |
| 119 | Single antiferromagnetic MnTe (sub)monolayers in CdTe/CdMgTe quantum wells. Semiconductor Science and Technology, 2000, 15, 506-510. | 1.0 | 7 |
| 120 | In situ reflectance difference spectroscopy of IIâ€“VI compounds: A real time study of N plasma doping during molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1697. | 1.6 | 1 |
| 121 | Reflectance difference spectroscopy and magneto-optical analysis of digital magnetic heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1722. | 1.6 | 1 |
| 122 | Control of morphology changes in self-assembled Mn-based nanostructures overgrown with mismatched material. Applied Physics Letters, 1999, 74, 3732-3734. | 1.5 | 5 |
| 123 | In situ reflectance difference spectroscopy: nitrogen-plasma doping of MBE grown ZnTe layers. Journal of Crystal Growth, 1999, 201-202, 132-136. | 0.7 | 3 |
| 124 | In situ characterization of the growth dynamics in molecular beam epitaxy (MBE) of Mn-based IIâ€“VI compounds: self-organized Mn structures on CdTe. Journal of Crystal Growth, 1999, 201-202, 707-710. | 0.7 | 2 |
| 125 | Magnetic polarons in MnTe layers. Journal of Magnetism and Magnetic Materials, 1999, 198-199, 194-196. | 1.0 | 0 |
| 126 | Reflectance Difference Spectroscopy of Mn Intra-Ion Transitions in p-Doped Diluted Magnetic Semiconductors. Physica Status Solidi (B): Basic Research, 1999, 215, 47-52. | 0.7 | 1 |

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| 127 | Assignment of reflectance difference spectroscopy peaks to IIâ€“VI surface layers. Journal of Crystal Growth, 1998, 184-185, 218-222. | 0.7 | 6 |
| 128 | MnTe fractional monolayers in CdTe/CdMgTe heterostructures: a comparative study of magnetic polarons. Journal of Crystal Growth, 1998, 184-185, 921-925. | 0.7 | 4 |
| 129 | Lattice-matched Zn1â^'yCdySe/InxGa1â^'xAs(0 0 1) heterostructures. Journal of Crystal Growth, 1998, 184-185, 21-25. | 0.7 | 1 |
| 130 | Schottky barrier tunability in Al/ZnSe interfaces. Journal of Crystal Growth, 1998, 184-185, 193-198. | 0.7 | 0 |
| 131 | Chemical bevelling of CdTe and CdTe/MnTe structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 55, 225-228. | 1.7 | 2 |
| 132 | Native extended defects in Zn[sub 1â^'y]Cd[sub y]Se/In[sub x]Ga[sub 1â^'x]As heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2334. | 1.6 | 1 |
| 133 | Lateral confinement in ZnSe/ZnCdSe quantum wells grown on patterned substrates. Applied Physics Letters, 1998, 72, 575-577. | 1.5 | 7 |
| 134 | Strain and surface morphology in lattice-matched ZnSe/InxGa1â^'xAs heterostructures. Journal of Applied Physics, 1998, 83, 2504-2510. | 1.1 | 10 |
| 135 | In situ reflectance difference spectroscopy of N-plasma doped ZnTe grown by molecular beam epitaxy. Applied Physics Letters, 1998, 73, 3857-3859. | 1.5 | 15 |
| 136 | Molecular beam epitaxy of ZnCdSe/ZnSe wires on patterned GaAs substrates. Journal of Crystal Growth, 1998, 184-185, 347-351. | 0.7 | 2 |
| 137 | Magneto-Optical Spectroscopy on Digital Magnetic Heterostructures. Physica Status Solidi A, 1997, 164, 331-334. | 1.7 | 2 |
| 138 | Electrical characterization of engineered ZnSeî—¸GaAs heterojunction diodes. Journal of Crystal Growth, 1997, 175-176, 603-607. | 0.7 | 3 |
| 139 | Evolution of deep levels and internal photoemission with annealing temperature at ZnSe/GaAs interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2961. | 1.6 | 6 |
| 140 | Structural properties of heterostructures with engineered band offsets. Journal of Crystal Growth, 1996, 159, 703-708. | 0.7 | 13 |
| 141 | Internal photoinjection and deep level luminescence at ZnSe/GaAs heterointerfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 867-871. | 0.9 | 3 |
| 142 | Recombination mechanisms in photopumped Zn1â^'xCdxSe/ZnSe multiple quantum well lasers. Journal of Crystal Growth, 1995, 150, 712-717. | 0.7 | 1 |
| 143 | Influence of growth parameters on the properties of ZnSe-GaAs(001) heterostructures. Journal of Crystal Growth, 1995, 150, 765-769. | 0.7 | 6 |
| 144 | Deep level formation at ZnSe/GaAs(100) interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1705. | 1.6 | 6 |

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